



STP210N75F6

N-channel 75 V, 3 m Ω , 120 A TO-220
STripFET™ VI DeepGATE™ Power MOSFET

Features

Order code	V _{DSS}	R _{DS(on)} max	I _D
STP210N75F6	75 V	< 3.7 m Ω	120 A

- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

Application

Switching applications

Description

This product is a 75 V N-channel STripFET™ VI Power MOSFET based on the ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

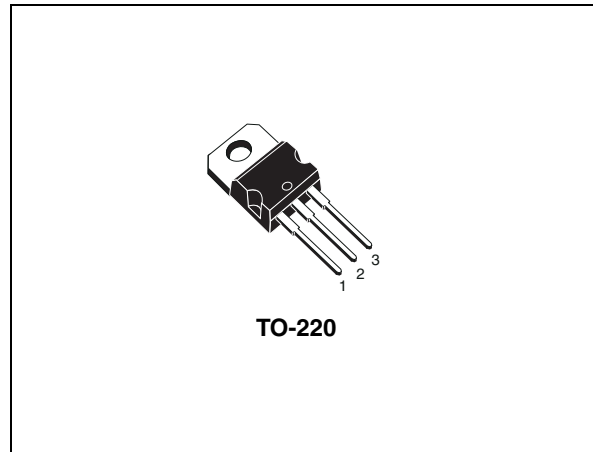


Figure 1. Internal schematic diagram

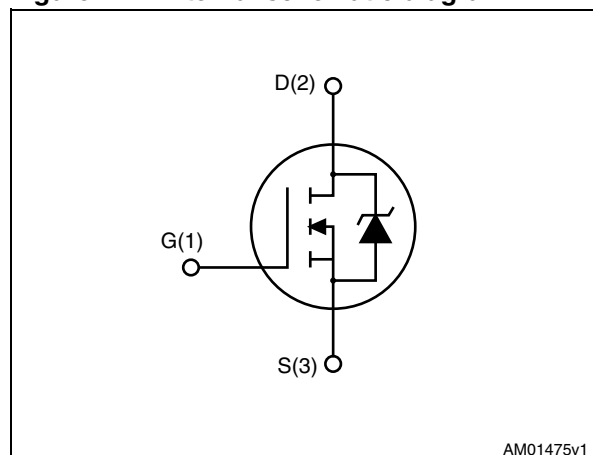


Table 1. Device summary

Order code	Marking	Package	Packaging
STP210N75F6	210N75F6	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	75	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(1)}$	Drain current (pulsed)	480	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
T_{stg}	Storage temperature	- 55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Current limited by package.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	75			V
I_{DSS}	Zero gate voltage	$V_{DS} = \text{max rating}$			1	μA
	Drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$, $T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 60\text{ A}$		3.0	3.7	$\text{m}\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			11800		pF
C_{oss}	Output capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1060	-	pF
C_{rss}	Reverse transfer capacitance				394	
Q_g	Total gate charge	$V_{DD} = 37.5\text{ V}$, $I_D = 120\text{ A}$, $V_{GS} = 10\text{ V}$ <i>(see Figure 14)</i>		171		nC
Q_{gs}	Gate-source charge			50		nC
Q_{gd}	Gate-drain charge				36	

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 40\text{ V}$, $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ <i>(see Figure 13)</i>	-	34	-	ns
t_r	Rise time			70		ns
$t_{d(off)}$	Turn-off-delay time	$V_{DD} = 40\text{ V}$, $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ <i>(see Figure 13)</i>	-	154	-	ns
t_f	Fall time			71		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 120\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_j = 150\text{ }^\circ\text{C}$ <i>(see Figure 15)</i>	-	60		ns
Q_{rr}	Reverse recovery charge			144		nC
I_{RRM}	Reverse recovery current			4.8		A

1. Current limited by package.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

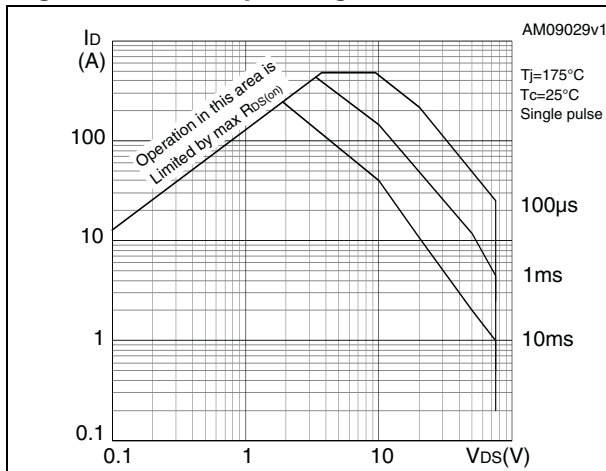


Figure 3. Thermal impedance

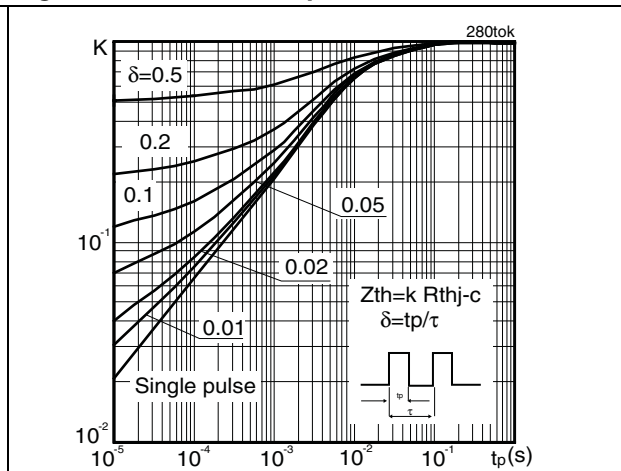


Figure 4. Output characteristics

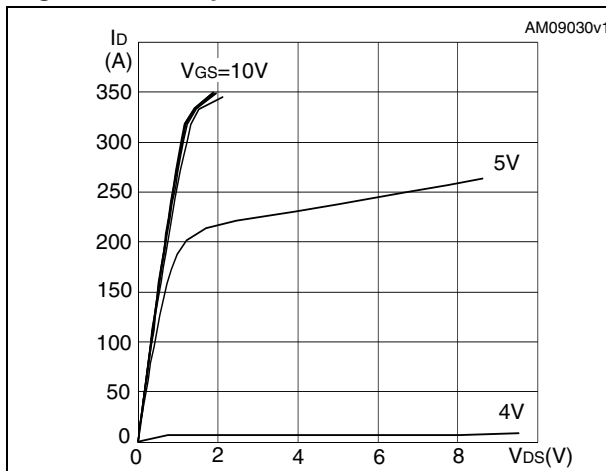


Figure 5. Transfer characteristics

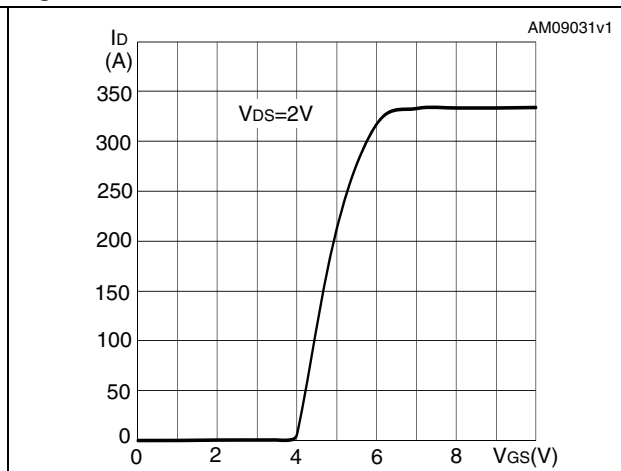


Figure 6. Normalized $B_{V_{DSS}}$ vs temperature

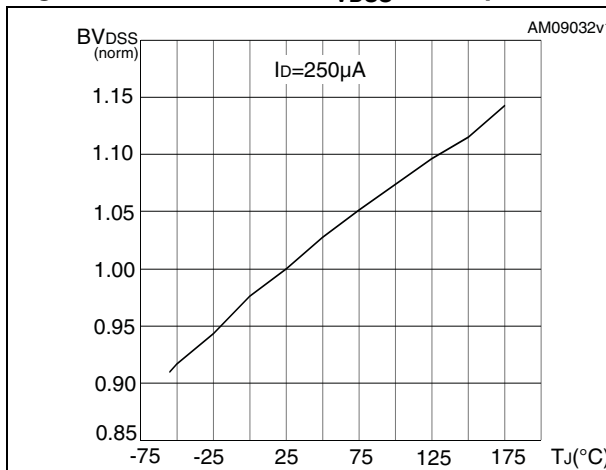


Figure 7. Static drain-source on resistance

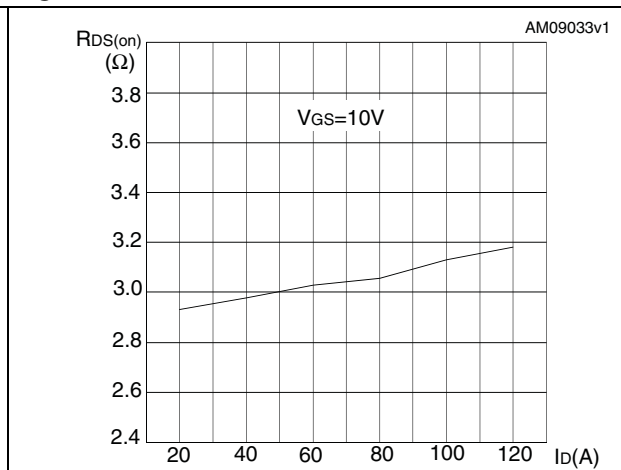


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

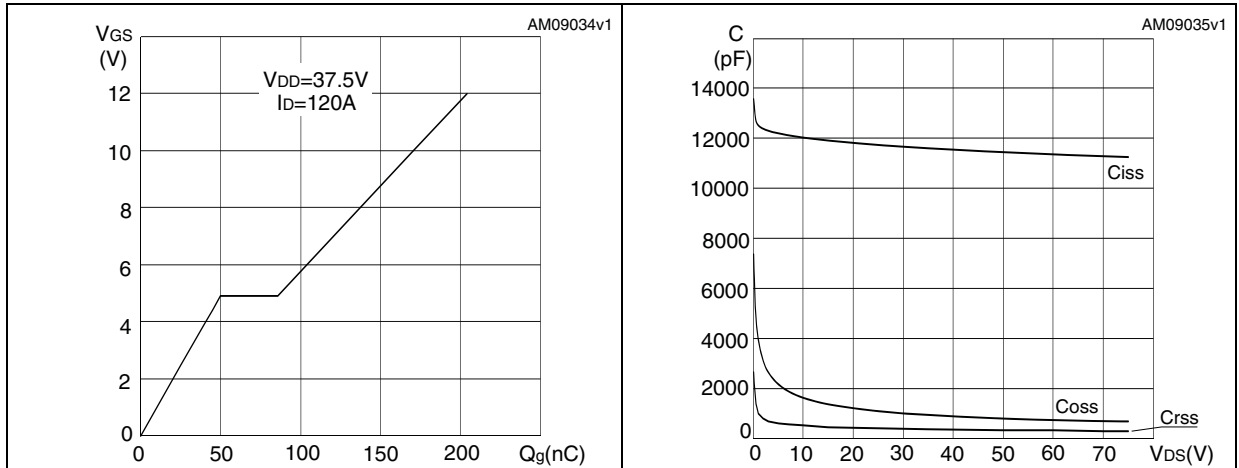


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

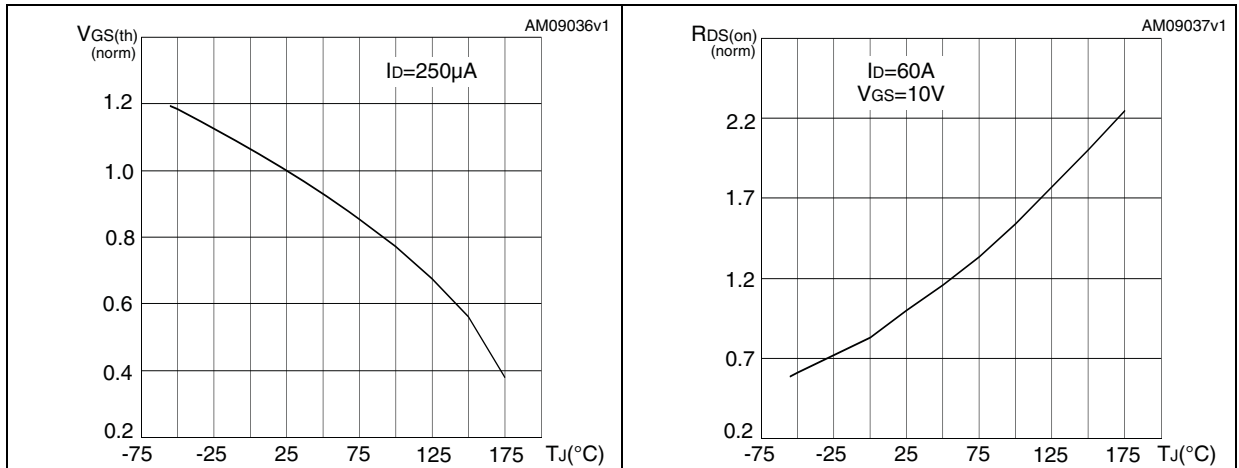
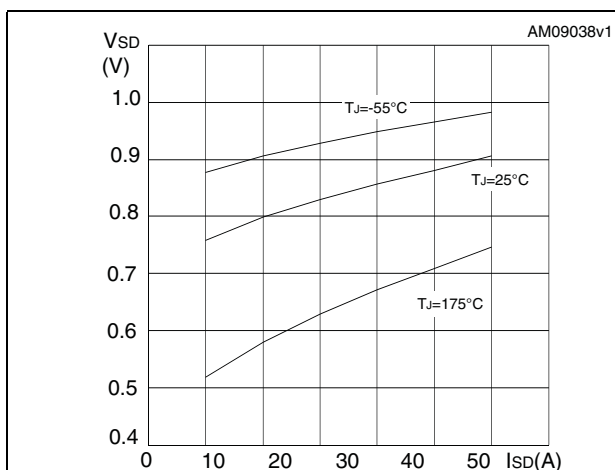


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

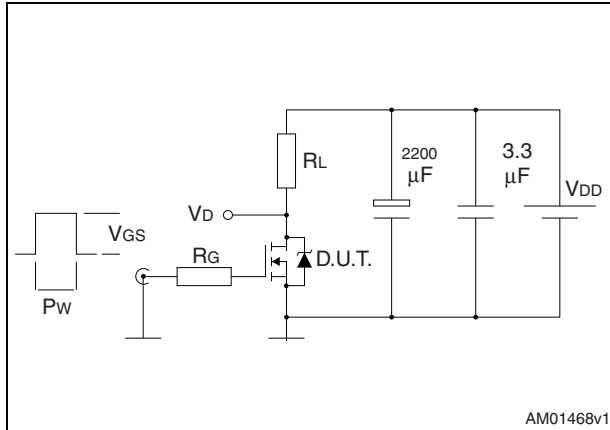


Figure 14. Gate charge test circuit

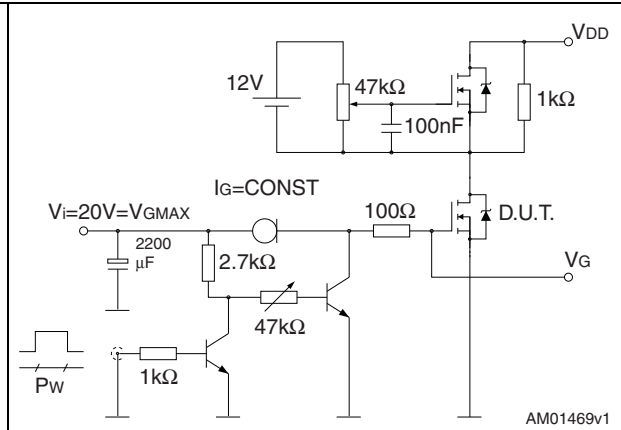


Figure 15. Test circuit for inductive load switching and diode recovery times

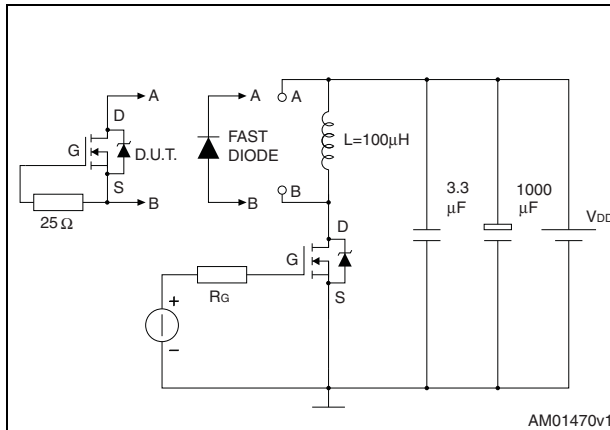


Figure 16. Unclamped inductive load test circuit

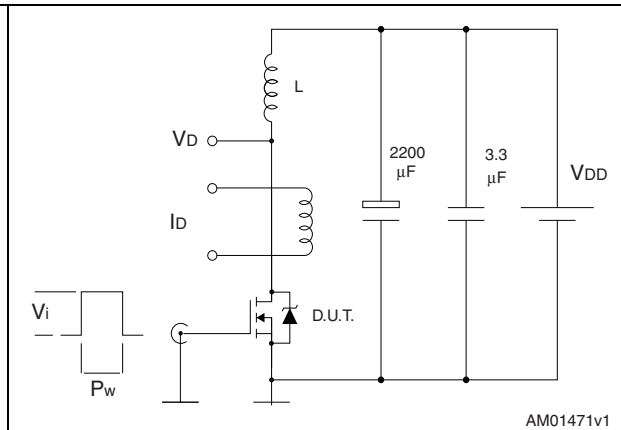


Figure 17. Unclamped inductive waveform

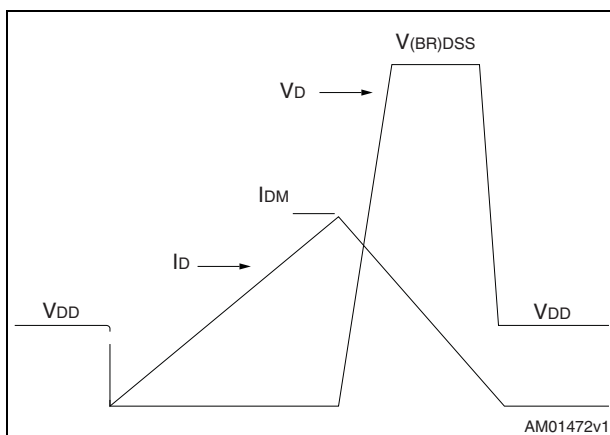
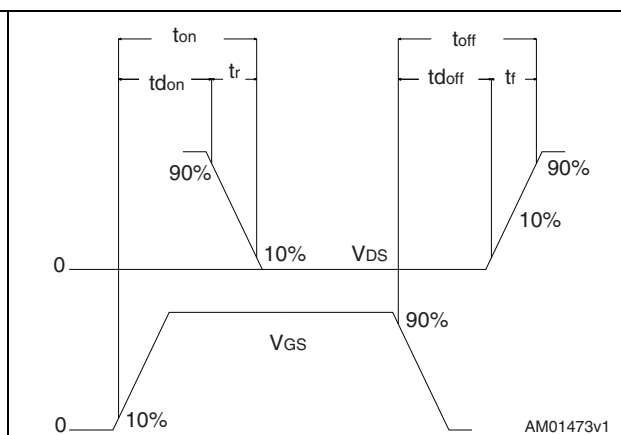


Figure 18. Switching time waveform



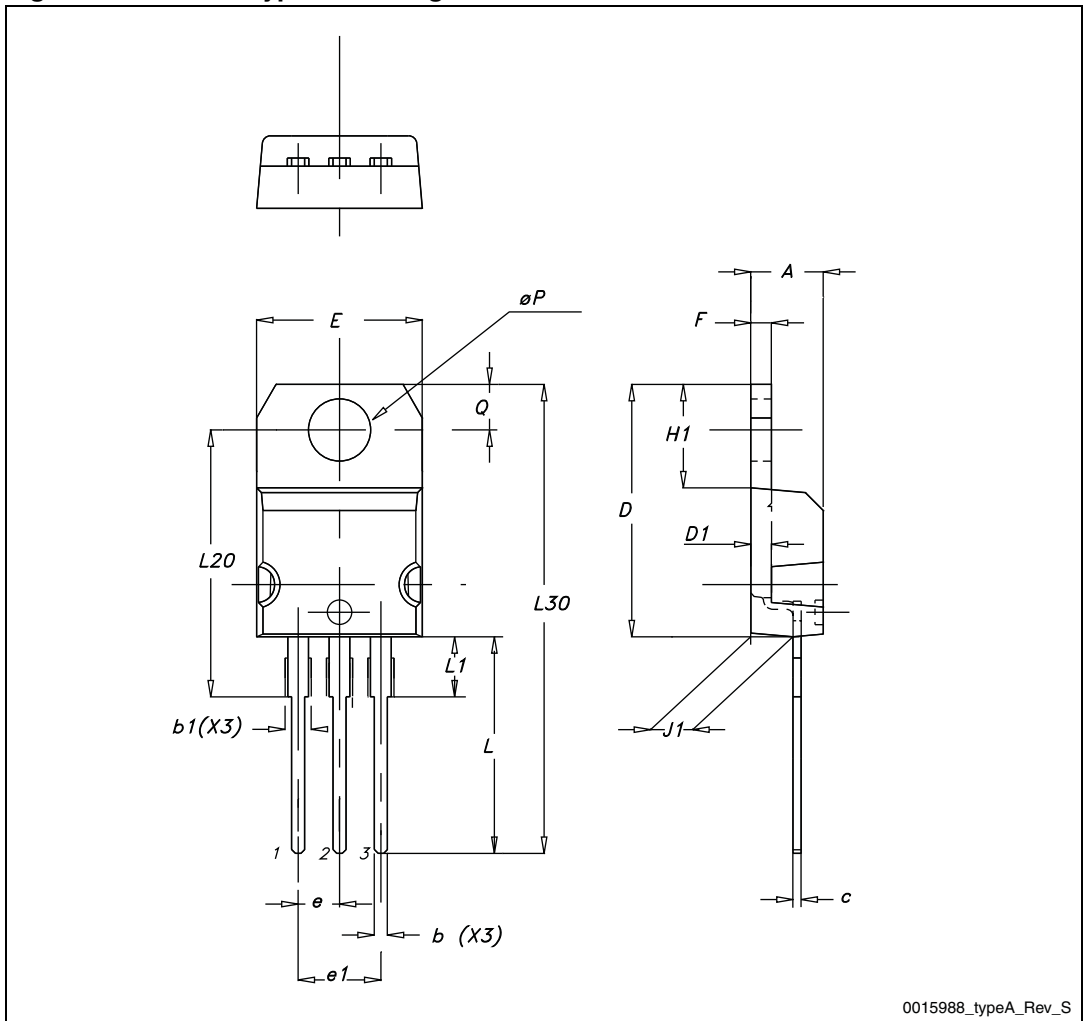
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
02-May-2011	1	First release.

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